



## Silicon Detectors in 3D-Technology

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-Part of this work is performed in the framework of the CERN RD50 Collaboration-



### Introduction



- 3D Detectors started 1996
- Harvesting 12 years later
  - 3D Projects in ATLAS, RD50,...
  - At PSD08, six 3D-related talks and posters

3D Detector Idea: Parker, Kenny, Segal, *NIM* **A395**, (1997) 328

#### Disclaimer:

At VERTEX 2008, Chris Parkes presented an overview of 3D detectors, see: http://indico.cern.ch/conferenceDisplay.py?confId=30356

Chris extensively covered 3D pixel detectors and processing. I will concentrate on 3D strips, especially STC.

## Motivation: The SLHC



- LHC Upgrade to Super-LHC (SLHC) planned for 2016:
  - Increase luminosity by factor ten compared to LHC
  - Massive increase of radiation dose for silicon detectors, making radiation damage the major concern
  - ATLAS will need to replace Inner Tracking system to cope with SLHC
  - Not clear if radiation hardness of planar Silicon pixel or strip detectors is sufficient



→ 3D designs investigated for SLHC pixel detectors

→ Study 3D short
 strip detectors
 (~2-3cm strip length)

#### Reminder: The 3D Principle

- 3D detectors decouple thickness (=signal) and depletion voltage
- Depletion and charge collection is sideways
- Superior radiation hardness "by design"
  - less trapping (as collection distances are short)
  - Full depletion voltage less affected by growing acceptor concentration (V<sub>dep</sub> ~ distance<sup>2</sup>)
- Original 3D designs
  - Brilliant but complex
  - conceived as pixel devices
  - can connect rows of columns to form strips



n-type substrate







## 3D Designs



- Original 3D
  - Good performance but costly and complex to manufacture
  - Mainly made for pixel applications
- Single Type Column (STC) 3D
  - Much simpler: columns on one side only
  - Produced successfully: Pixel and strip detectors exist
  - STCs tested extensively
- Double Type Column (DTC) 3D
  - Better than STC, yet simpler than classic 3D
  - The next step in "simpler 3Ds"



3D STC strip detector







- STC sensors made by FBK-irst (Trento)
- Initial fast lateral depletion at 5V for FZ Si
- Then depleting like a planar detector
- Low field in central region remains
  - indep. of bias voltage
  - bias affects only field under columns towards back side

#### xy-null field lines





#### 3D STC Module with FZ sensors





- 3D STC strip detectors are *"like planar strips plus columns under the strips"* 
  - 80µm strip pitch, 80µm or 100µm column pitch
  - 300µm thick
  - 64 strips, 2cm strip length
  - Si: FZ p-spray or FZ p-stop



FZ p-stop sensor





#### Noise Behaviour



- 3D devices will have higher capacitance (and noise!) than planar designs
- Measure noise at LHC readout speed (40MHz)
- Noise is
  - Uniform across sensor
  - Rapidly decreasing with bias voltage until lateral full depletion at ≈ 25V
  - Then slowly decreasing as sensor continues to deplete towards backside
  - Typical noise 1200 ENC (corresponds to 6-7cm strips in planar design)
- Micro-discharge starting at 95V (before sensor is fully depleted)



### Signal: IR Laser Measurements



- Three methods available to generate charge in Si:
  - Laser
  - Radioactive source
  - High-energy particles (MIP)
- Example: pulsed IR Laser
  - Focused to 5µm spot size
  - Coupled into fiber
  - Scan detector surface to study uniformity of charge collection efficiency
  - Scan area is unit cell
- Narrow region of lower CCE (≈5µm) on p-spray sensor
- Likely cause is central low field region
- Signal drops by ≈25% 30%











- Test before and after irradiation to 10<sup>15</sup>N<sub>eq</sub>/cm<sup>2</sup>
- Charge collection is reduced by irradiation
- Given sufficient HV stability, the irradiated detector collects the same charge as prior to irradiation
- V<sub>FD</sub> ~ 230V as predicted for CZ p-type

3D STC on CZ p-type Si





## 2007 Beam Test



- Two 3D STC detectors were tested with 180GeV SPS Pions in Autumn 2007
- Main aim: position-resolved study of CCE, signal and signal shape
- Signal measurement with ADC Calibration: Landau MPV at 2.4 fC (70% of 3.5 fC)
- Note: Entire Test Beam analysis still preliminary
  - work on tracking & alignment ongoing



### Efficiency in Beam Test

- Alignment much better <u>orthogonal</u> to strips due to small beam shape
- Study 1-D efficiency orthogonal to strip
  - number of hits on 3D matched to tracks as a function of distance to strip "residual"
  - map entire detector onto one strip
- Low efficiency at
  - large distance to strip: low field region
  - strip center: no charge deposition in hollow columns







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### Comments on 3D-STCs



- Overall charge level low (~2.3fC) due to ballistic deficit arising from 3D-STC field configuration
- 3D-STC after irradiation to 10<sup>15</sup>N<sub>eq</sub>/cm<sup>2</sup> are still operational
- Same CCE as unirradiated device, but at much higher bias voltage
- 3D STC designs are first steps towards simple costeffective 3Ds



Need to move from STC to DTC!

#### Double-sided 3D detectors

- Improved 3D structure proposed by G. Pellegrini (CNM): n- and p-type columns etched from opposite sides
- Similar design (DDTC) produced independently by FBK-irst (Trento)
  - Columns do not pass through full substrate thickness
  - Reduces low field regions, field becomes driven by bias voltage
- Expect faster signals and higher CCE
- Should compare well to conventional 3D design







- First detectors exist
- Simulations predict superior radition hardness



## First DTC Results: Strip detector IV

- CNM 3D DTC detectors
- 128 strips, 50 holes/strip, pitch 80µm, length 4mm
- Strip currents ~100pA (T=21°C) in all 4 detectors
- Can reliably bias detectors to 50V (20 times lateral depletion voltage), no breakdown
- Capacitance 5pF / strip
- Guard ring currents vary:
  - Highest 20µA at 10V
  - Lowest 0.03µA at 50V
- Irradiated with 5.10<sup>15</sup>
  N<sub>eq</sub> in Ljubljana
- IV curves roughly as expected for fluence



Ulrich Parzefall, Universität Freiburg





## Conclusions & Outlook



- Extensive tests on modules with STC 3D detectors. STCs are functional detectors, and radiation hard
  - Too slow for a 40 MHz SLHC (field configuration)
- Radiation hardness of planar designs can be increased with equivalent 3D design
  - higher noise, higher price
  - ATLAS has large 3D program for pixel detector underway
- Future 3D tests will concentrate on DTC devices
  - Simulations and first tests indicate faster charge collection
  - 2008 Test Beam (CMS/RD50) data are on tape

#### Related Talks & Posters:

- G. Pellegrini "Fabrication and simulation of Novel Ultra Thin 3D Silicon Detectors..."
- D. Gunning "High spacial resolution probes for neurobiology applications"
- N. Wermes "Pixel detectors for charged particles "
- C. Fleta "Characterization of double-sided 3D Medipix 2 detectors"
- F.G. Huegging "Sensor concepts for future hybrid pixel detectors"
- A. Zoboli "Laser and beta source setup characterization of 3D DDTC detectors... "









## **3D Results Overview**



- Summary of results from planar and 3D detectors by Cinzia
- Superior radiation hardness (ATLAS 3D pixel collaboration)
- Results for 3D strip detectors above 10<sup>15</sup>N<sub>eq</sub> still unavailable



## **Opposite Polarity Signals**

0.5

-0.5

20

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40

60

V

X



- 3D STC: Opposite polarity signals on neighbouring strips
- Seen very clearly in Laser
- Also visible in Beam Test
  - Traditional clustering algorithms would fail
- Effect only observable for neighbouring strips, but must also be present within one strip
  - low charge for hits between columns of the same strip
- Reason is field configuration
  - charges drift mainly sideways to/away from columns
  - low field means slow hole drift to backside, t<sub>drift</sub> >25ns
- This is an effect of STC design
- Given sufficient statistics and resolution, this could be visible in Test Beam analysis



**Beam Test:** 

Signal on neighbour

80

100

120 time [ns]





- Single Type Column (STC) 3D design:
  - Columns not completely etched through wafer → no support wafer necessary
  - STC sensors made by FBK-irst (Trento)
- Processing less complex and costly compared to standard 3D
- Si bulk can be n-in-p material
  - no type-inversion
  - Collection of e- (faster, less trapping)
  - Wafers: Czochralski or Floatzone-Si
  - P-spray or p-stop isolation (to avoid conductive layer between n-implants)
- Low field region exists (slow drift)
  - field given by doping level (not U<sub>bias</sub>)
  - LHC is fast, so expect reduced CCE at 40 MHz
  - 3D STC strip designs interesting for innermost strip layers Electrons are swept
  - 3D STC strip detectors are away by the "*like planar strips plus columns under the strips*"



50µm

# High Resolution Laser Scan





>200 il ui leus il 150 50 is 0

- $2\mu$ m step size
- 50µm×50µm area
- y-axis along the strips
- At variable bias voltage

 $V_{bias} = 50V$ 

-0.05

-0.06 m<sup>1</sup>



-0.08



-0.08















-0.03-0.04 -0.3 -0.25 -0.2 -0.15 -0.1

0.1

0

 $-0.05 \ 0 \ x_{s} [mm]$ 



